L Number	Hits	Search Text	DB	Time stamp
1	2908855	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:31
2	152746	(memory or storage) and (nonvolatile or non-volatile or floating adj gate or charge adj2 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:23
4	973	((memory or storage) and (nonvolatile or non-volatile or floating adj gate or charge adj2 layer)) and cell with bit with (left or right)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:04
5	10	(((memory or storage) and (nonvolatile or non-volatile or floating adj gate or charge adj2 layer)) and cell with bit with (left or right)) and compar$5 with (detect$5 or check$5) with (first or left or right) with bit	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:10
6	4556	(memory or storage) and two adj bit with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:12
7	2016	((memory or storage) and (nonvolatile or non-volatile or floating adj gate or charge adj2 layer)) and ((memory or storage) and two adj bit with cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:13
8	623	(((memory or storage) and (nonvolatile or non-volatile or floating adj gate or charge adj2 layer)) and ((memory or storage) and two adj bit with cell)) and read$5 with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:33
9	0	((((memory or storage) and (nonvolatile or non-volatile or floating adj gate or charge adj2 layer)) and ((memory or storage) and two adj bit with cell)) and read$5 with (voltage or potenital or level) with drain) and write adj verify with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:15
10	0	((((memory or storage) and (nonvolatile or non-volatile or floating adj gate or charge adj2 layer)) and ((memory or storage) and two adj bit with cell)) and read$5 with (voltage or potenital or level) with drain) and write-verify with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:15
11	0	((memory or storage) and two adj bit with cell) and write-verify with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:33
12	2	((memory or storage) and two adj bit with cell) and write near2 verify with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:16
13	86406	(memory or storage) and trap$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:24
14	1339	((memory or storage) and trap$5) and read$4 with drain with (voltage or potential or level)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:26
16	5	(((memory or storage) and trap$5) and read$4 with drain with (voltage or potential or level)) and write adj verify with drain with (voltage or potenital or level)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:27
17	201013	(memory or storage) and (two or '2') near2 (bit or state or threshold or level)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:33

18	2464	((memory or storage) and (two or '2') near2 (bit or state or threshold or level)) and read$5 with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:33
19	1	(((memory or storage) and (two or '2') near2 (bit or state or threshold or level)) and read$5 with (voltage or potenital or level) with drain) and write-verify with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:35
20	0	(((memory or storage) and (two or '2') near2 (bit or state or threshold or level)) and read$5 with (voltage or potenital or level) with drain) and writing near2 verify with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:37
21	0	(((memory or storage) and (two or '2') near2 (bit or state or threshold or level)) and read$5 with (voltage or potenital or level) with drain) and writing near2 verifying with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:37